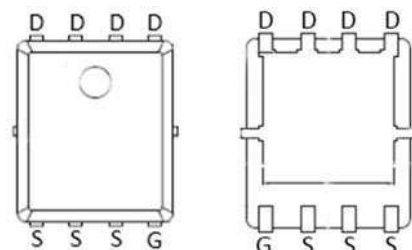
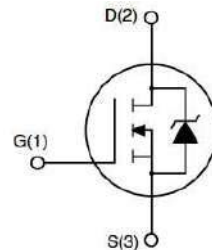


TPG011N03G

N-Channel Enhancement Mosfet

Feature

- 30V,180A
 $R_{DS(ON)} < 1.1m\Omega @ V_{GS}=10V$ TYP=0.9 m Ω
 $R_{DS(ON)} < 1.7m\Omega @ V_{GS}=4.5V$ TYP=1.5 m Ω
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



PDFN5X6-8L

Application

- PWM applications
- Load Switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G011N03G	TPG011N03G	PDFN5*6-8L	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	180	A
Continuous Drain Current ($T_a=100^{\circ}C$)	I_D	120	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	378	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	160	mJ
Power Dissipation	P_D	59	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.5	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =± 20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.7	2.2	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =10V, I _D =40A	-	0.9	1.1	mΩ
		V _{GS} =4.5V, I _D =20A	-	1.5	1.7	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f =1000KHz	-	3800	-	pF
Output Capacitance	C _{oss}		-	2400	-	
Reverse Transfer Capacitance	C _{rss}		-	35	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =15V, I _D =15A, R _L =10Ω V _{GS} =10V, R _G =3Ω	-	16.6	-	ns
Turn-on rise time	t _r		-	48.2	-	
Turn-off delay time	t _{d(off)}		-	66	-	
Turn-off fall time	t _f		-	20.4	-	
Total Gate Charge	Q _g	V _D S=15V, I _D =15A, V _G S=4.5V	-	31	-	nC
Gate-Source Charge	Q _{gs}		-	8.6	-	
Gate-Drain Charge	Q _{gd}		-	15	-	
Reverse Recovery Chrage	Q _{rr}	I _F =15A,di/dt=100A/us		124		nC
Reverse Recovery Time	T _{rr}	I _F =15A,di/dt=100A/us		84		ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =10A	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I _S		-	-	180	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^{\circ}\text{C}, V_{DD} = 27V, R_G = 25\Omega, L = 0.3\text{Mh}, I_{AS} = 32A$
3. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$

Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

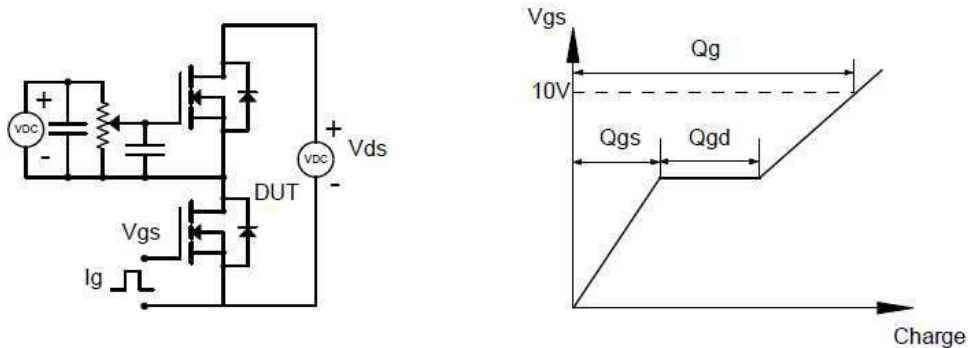


Figure B: Resistive Switching Test Circuit & Waveforms

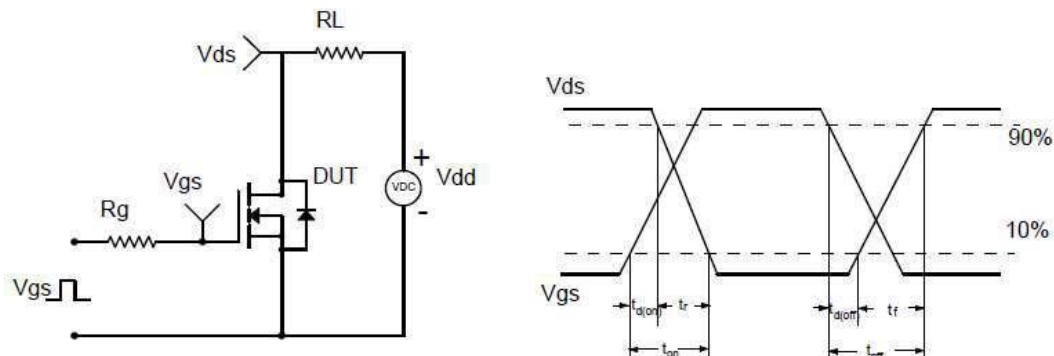


Figure C: Unclamped Inductive Switching (UIS) Test

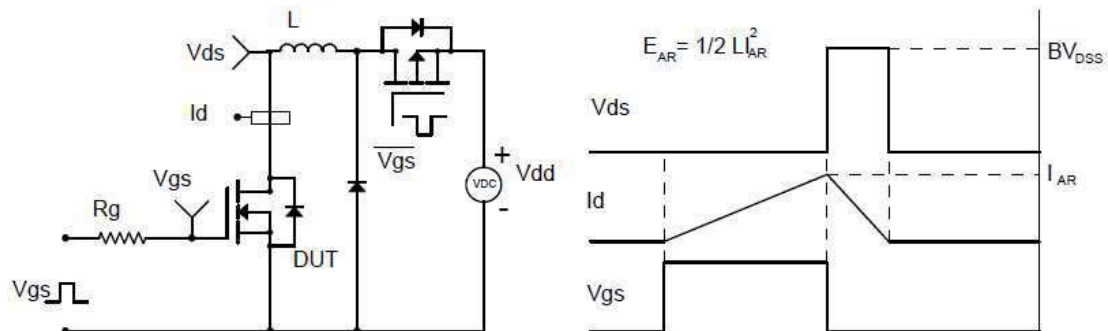
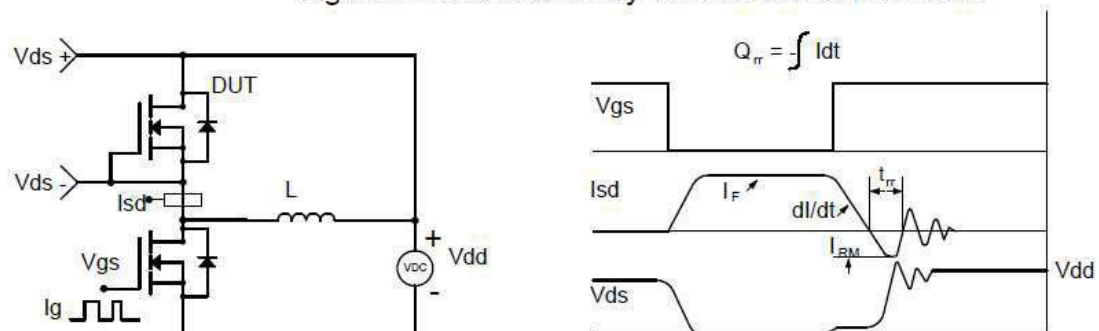
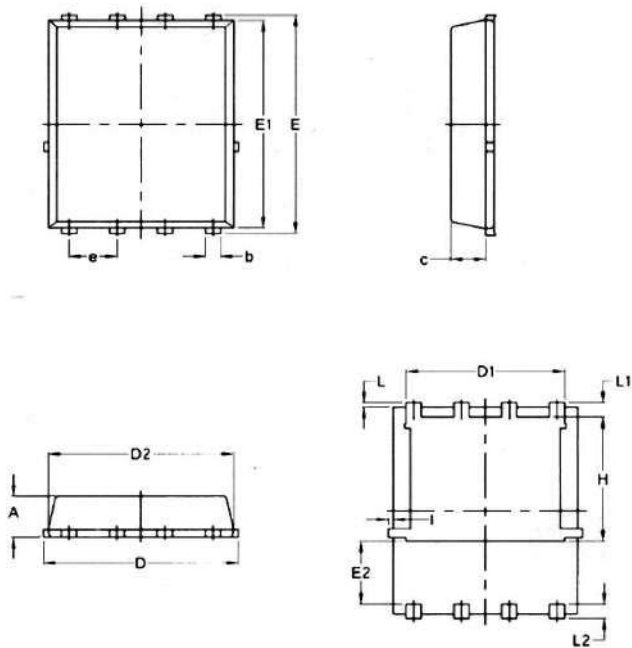


Figure D: Diode Recovery Test Circuit & Waveforms



PDFN5*6-8L Package Information



PDFN5X6-8L

SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	—	0.0630	—
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	—	0.18	—	0.0070